18V N-Channel Trench Power MOSFET

General Description

The SJM18N031 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a wide variety of applications.

Features

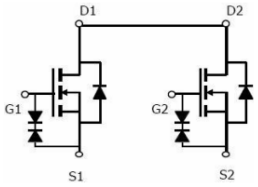
- Low Gate Charge
- High Power and current handing capability
- Lead free product is acquired
- ESD Rating: HBM 2KV

Application

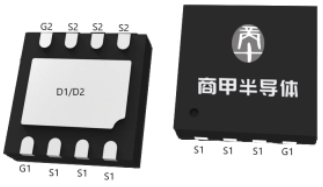
- Load Switch

Key Performance Parametes

Parameter	Value	Unit
V_{DS}	18	V
$R_{DS(ON)\_TYP}$	3.1	mΩ
I_D	70	A
Q_G	38	nC



Schematic Diagram



DFN3X3-8L top&bottom view

RoHS

Package Marking and Ordering Information

Device/Ordering Code	Marking	Package	Packing	Reel Size	Tape width	Quantity
SJM18N031	SJM18N031	DFN3X3-8L	Tape	\	\	5000 Pcs

Table 1. Absolute Maximum Ratings (T_C=25℃ unless otherwise noted)

Symbol	Parameter	Limit	Unit
V_{DS}	Drain-Source Voltage (V_{GS}=0V)	18	V
V_{GS}	Gate-Source Voltage (V_{DS}=0V)	±10	V
I_D	Drain Current-Continuous(T_C=25℃)	70	A
	Drain Current-Continuous(T_C=100℃)	44	A
$I_{DM\ (pluse)}$	Drain Current-Continuous@ Current-Pulsed (Note 1)	280	A
P_D	Maximum Power Dissipation(T_C=25℃)	27	W
	Maximum Power Dissipation(T_C=100℃)	11	W
E_{AS}	Avalanche energy (Note 2)	196	mJ
T_J, T_{STG}	Operating Junction and Storage Temperature Range	-55 To 150	℃

Table 2. Thermal Characteristic

Symbol	Parameter	Typ	Max	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case		4.7	℃/W

Table 3. Electrical Characteristics (T_J=25℃ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
On/Off States						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V I_D=250μA	18			V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=18V, V_{GS}=0V T_J=25℃			1	μA
		V_{DS}=18V, V_{GS}=0V T_J=125℃			100	μA
I_{GSS}	Gate-Body Leakage Current	V_{GS}=±10V, V_{DS}=0V			±10	uA
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D=250μA	0.5		1	V
g_{FS}	Forward Transconductance	V_{DS}=5V, I_D=8A		45		S
$R_{DS(ON)}$	Drain-Source On-State Resistance	V_{GS}=4.5V, I_D=8A T_J=25℃		3.1	3.9	mΩ
$R_{DS(ON)}$	Drain-Source On-State Resistance	V_{GS}=2.5V, I_D=6A T_J=25℃		3.9	5.2	mΩ
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS}=9V,V_{GS}=0V, f=100KHz		3700		pF
C_{oss}	Output Capacitance			371		pF
C_{rss}	Reverse Transfer Capacitance			344		pF
R_g	Gate resistance	V_{GS}=0V, V_{DS}=0V, f=100KHz		886		Ω
Switching Parameters						
$t_{d(on)}$	Turn-on Delay Time	V_{GS}=4.5V, V_{DS}=9V, R_L=1.1Ω, R_{GEN}=3Ω		11		nS
t_r	Turn-on Rise Time			34		nS
$t_{d(off)}$	Turn-Off Delay Time			72		nS
t_f	Turn-Off Fall Time			92		nS
Q_g	Total Gate Charge	V_{GS}=4.5V, V_{DS}=9V, I_D=8A		38		nC
Q_{gs}	Gate-Source Charge			7		nC
Q_{gd}	Gate-Drain Charge			10		nC
Source-Drain Diode Characteristics						
I_{SD}	Source-Drain Current (Body Diode)				70	A
V_{SD}	Forward on Voltage (Note 3)	V_{GS}=0V, I_S=8A			1.2	V
t_{rr}	Reverse Recovery Time	I_F=8A, dI/dt=100A/μs		16		ns
Q_{rr}	Reverse Recovery Charge	I_F=8A, dI/dt=100A/μs		5.5		nC

Notes 1.Repetitive Rating: Pulse width limited by maximum junction temperature.
Notes 2.E_{AS} condition: T_J=25℃,V_{DD}=10V,V_G=10V, Rg=25Ω, L=0.5mH.
Notes 3.Repetitive Rating: Pulse width limited by maximum junction temperature.

Typical Electrical And Thermal Characteristics (Curves)

Figure 1. Output Characteristics

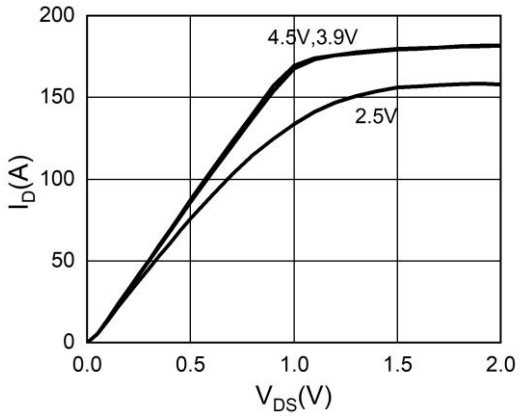


Figure 2. Transfer Characteristics

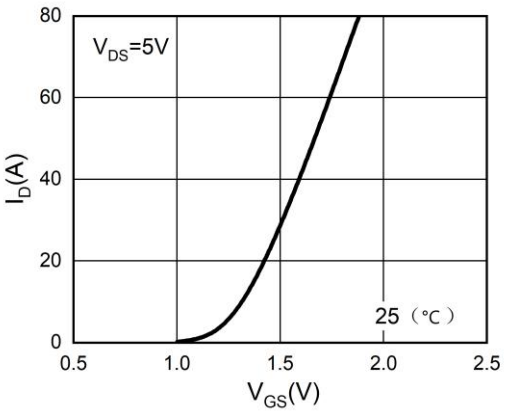


Figure 3. Power Dissipation

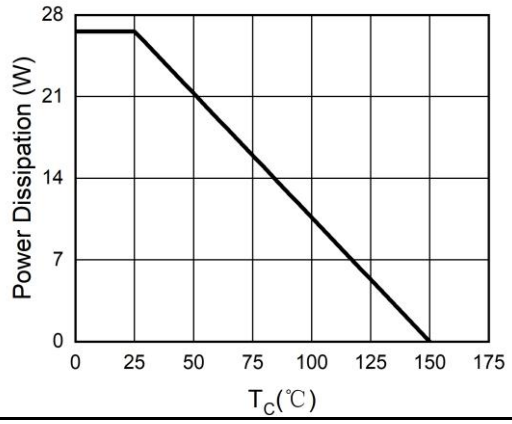


Figure 4. Drain Current

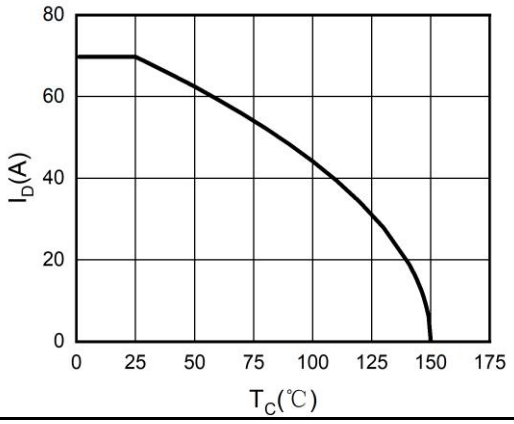


Figure 5. BV_{DSS} vs Junction Temperature

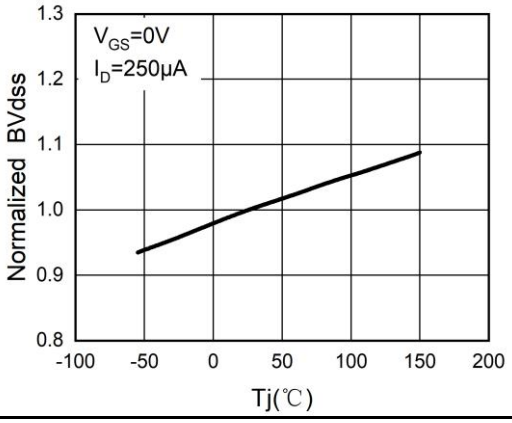
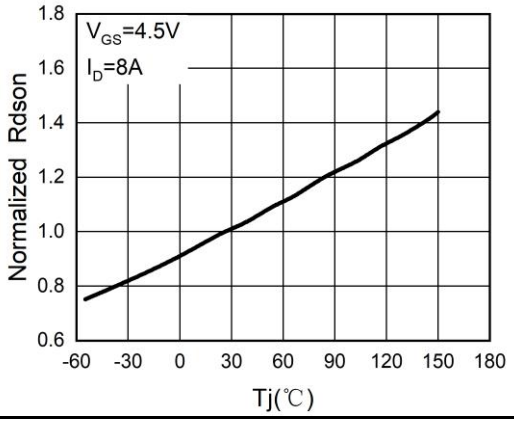


Figure 6. $R_{DS(ON)}$ vs Junction Temperature



Typical Electrical And Thermal Characteristics (Curves)

Figure 7. Gate Charge Waveforms

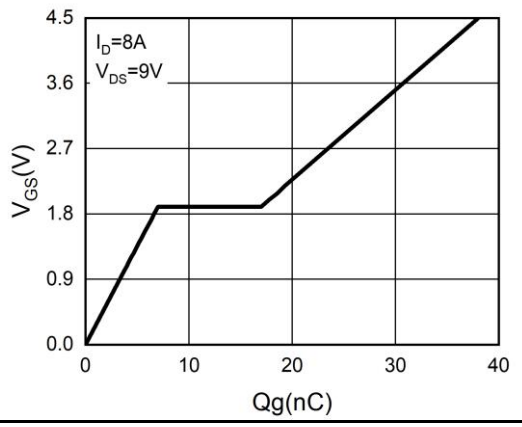


Figure 8. Capacitance

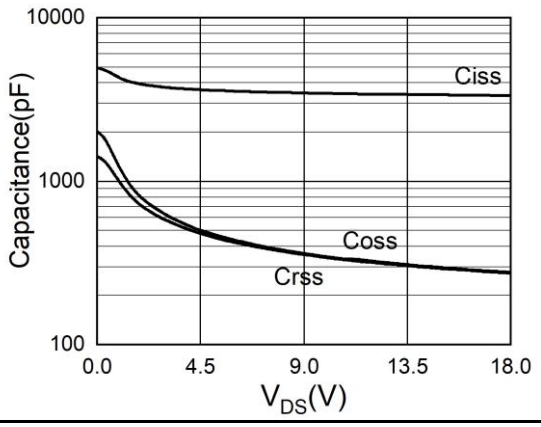


Figure 9. Body-Diode Characteristics

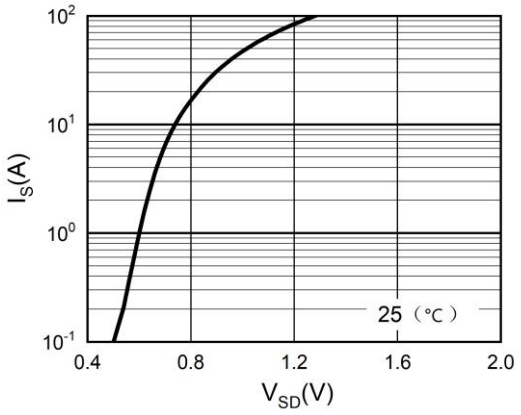
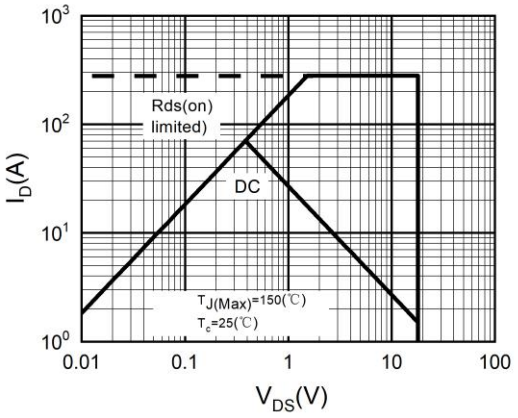
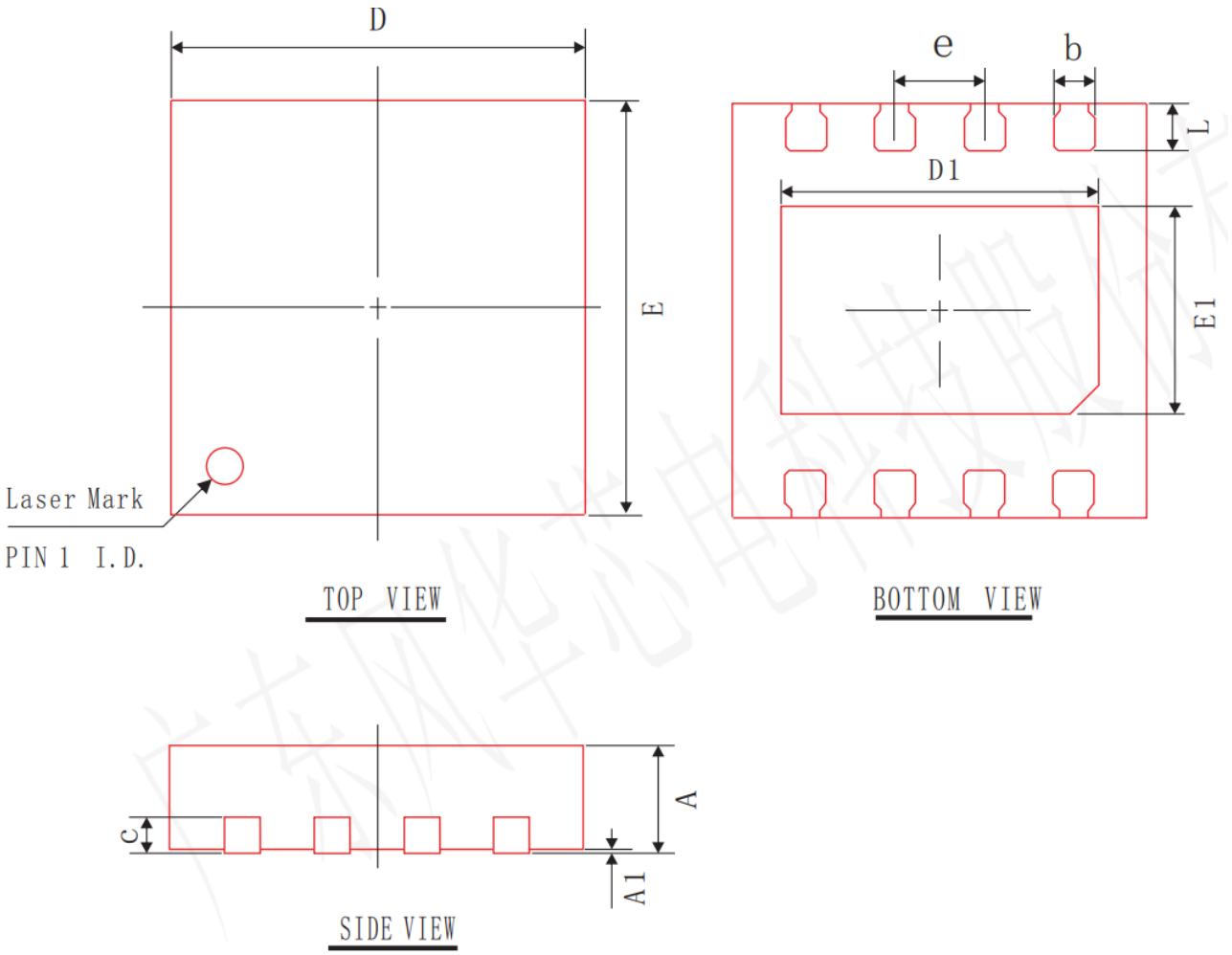


Figure 10. Maximum Safe Operating Area



DFN3X3-8L Package Information



COMMON DIMENSIONS
(UNITS OF MEASURE=mm)

SYMBOL	MIN	NOM	MAX
A	0.70	0.75	0.80
A1	0.00	0.02	0.05
b	0.25	0.30	0.35
D	2.95	3.00	3.07
E	2.95	3.00	3.07
D1	2.25	2.30	2.35
E1	1.40	1.50	1.60
L	0.25	0.35	0.45
c	0.203 REF		
e	0.65 BSC		

其它厚度尺寸如下

A	0.55	0.60	0.65
A	0.50	0.55	0.60

Attention

This product described in this document can not be used in life support devices or systems, aircraft's control systems, and other applications whose failure can be reasonably expected to result in serious physical and/or material damage，apart from that when an application agreement is signed between customer and Wuxi Shangjia Semiconductor.

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